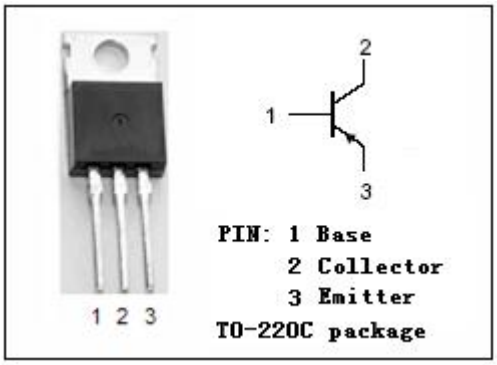
isc Silicon PNP Power Transistor — BD244C



DESCRIPTION

- DC Current Gain -h_{FE} =30(Min)@ I_C= -0.3A
- Complement to Type BD243C
- 100% tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

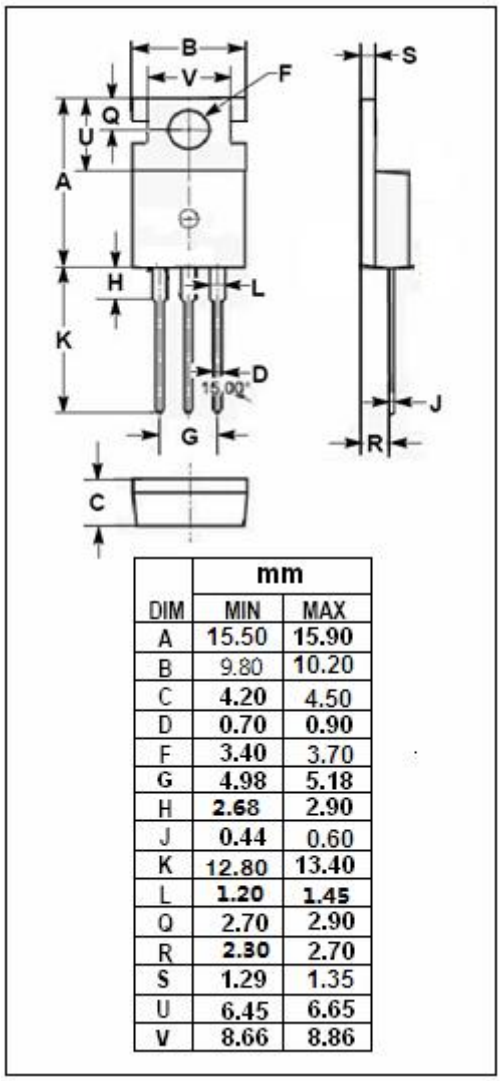
- Designed for use in general purpose power amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-6.0	A
I_{CM}	Collector Current-Peak	-10	A
I_B	Base Current	-2.0	A
P_C	Collector Power Dissipation @ T_C=25℃	65	W
T_J	Junction Temperature	-65~150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.92	℃/W



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -30mA ;I_B=0	-100		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -6A; I_B= -1A		-1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -6A ; V_{CE}= -4V		-2.0	V
I_{CES}	Collector Cutoff Current	V_{CE}= -100V; V_{BE}= 0		-0.4	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= -60V;I_B= 0		-0.7	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0		-1.0	mA
h_{FE-1}	DC Current Gain	I_C= -0.3A ; V_{CE}= -4V	30		
h_{FE-2}	DC Current Gain	I_C= -3A ; V_{CE}= -4V	15		
f_T	Current-Gain—Bandwidth Product	I_C= -0.5A ; V_{CE}= -10V, f_{test}= 1.0MHz	3.0		MHz